

# SILICON PNP TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

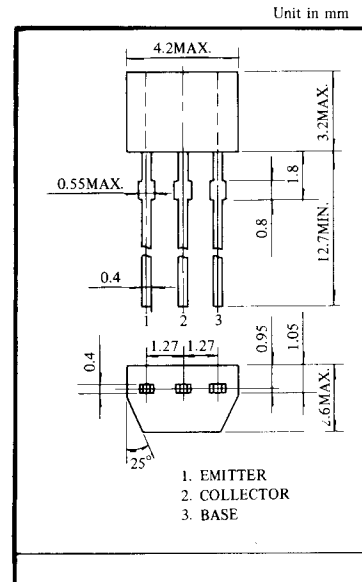
# 2SA1272

## APPLICATION

- Low Frequency Amplifier Applications.

## FEATURES

- High  $h_{FE}$ :  $h_{FE}=100\sim320$ .
- Complementary to 2SC3204.



## MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-35	V	Emitter Current	$I_E$	800	mA
Collector-Emitter Voltage	$V_{CEO}$	-30	V	Collector Power Dissipation	$P_C$	300	mW
Emitter-Base Voltage	$V_{EBO}$	-5	V	Junction Temperature	$T_J$	125	°C
Collector Current	$I_C$	-800	mA	Storage Temperature Range	$T_{stg}$	-55~125	°C

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=-30V, I_E=0$	-	-	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA$	-30	-	-	V
Dc Current Gain	$h_{FE(1)NOTE}$	$V_{CE}=-1V, I_C=-100mA$	100	-	320	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-700mA$	35	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=-500mA, I_B=-20mA$	-	-	-0.7	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=-1V, I_C=-10mA$	-0.5	-	-0.8	V
Transition Frequency	$f_T$	$V_{CE}=-5V, I_C=-10mA$	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10V, f=1MHz$	-	19	-	pF

## NOTE: According to $h_{FE(1)}$ Classified as follows.

0	100~200	Y	160~320
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